

FORM 1349 INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 10873.792US01	Application Number: 09/931,113
	Applicant: HIRAMOTO et al.	
	Filing Date: August 16, 2001	Group Art Unit: 1646

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MSL	5,953,248	Sept. 1999	Chen et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

MSL	S. Cardoso et al.; "High thermal stability tunnel junctions"; Journal of Applied Physics; Vol. 87, No. 9; May 1, 2000; pp. 6058-6060
MSL	Proceedings of 112th Study Group of the Magnetism Society of Japan, pp. 35-42



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EXAMINER	<i>[Signature]</i>	DATE CONSIDERED	10/30/03
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.			

FORM 1449*

INFORMATION DISCLOSURE STATEMENT

IN AN APPLICATION

(Use several sheets if necessary)

Docket Number:

10873.792US01

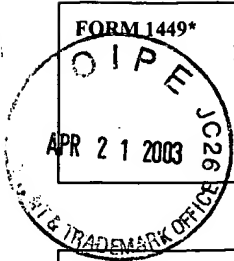
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Group Art Unit:



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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
NSU	5,650,958	07.1997	GALLAGHER ET AL.			
	5,390,061	02.1995	NAKATANI ET AL.			
	5,408,377	04.1995	GURNEY ET AL.			
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FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
NSU	0 913 830	05.1999	EP				
	1 033 764	09.2000	EP				
	199 34 009	01.2000	DE				SEE IDS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

NSU	Parkin S S P et al: "Exchange-Biased Magnetic Tunnel Junctions and Application to Nonvolatile Magnetic Random Access Memory (Invited)", Journal of Applied Physics, American Institute of Physics. New York, US, Vol.85, No. 8, April 15, 1000, PP 5828-5833.
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	Sakakima H et al: "Enhancement of MR ratios using thin oxide layers in PtMn and alpha-Fe203-based spin valves" Journal of Magnetism and Magnetic Materials, Elsevier Science Publishers, Amsterdam, NL, Vol. 210, No. 1-3, February 2000, PP 20-24
	Cardoso S et al: "High Thermal Stability Tunnel Junctions", Journal of Applied Physics, American Institute of Physics, New York, US, Vol. 87, No. 9, May 1, 2000, PP 6058-6060.

EXAMINER

DATE CONSIDERED

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